OKI semiconductor MSM16811P

1.024 BIT SERIAL E²PROM

FEATURES:

- CMOS Floating Gate Technology
- Single +5-volt supply
- Eight pin plastic package
- 64 x 16 or 128 x 8 user selectable serial memory
- Compatible with NS9346
- Self timed programming cycle with Auto erase
- Word and chip erasable
- Operating Range –40°C to 85°C
- 10,000 erase/write cylces
- 10 year data retention





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| PIN FUNCTIONS | | | | | | |
|--|--|-----|--|--|--|--|
| CS SK DI DO VCC NC GND | Chip Select Clock Input Serial Data Input Serial Data Output +5 V Power Supply Non Connection Ground | ORG | Memory Array Organization Selec- tion Input. When the ORG pin is connected to +5 V the 64 x 16 organization is selected. When it is connected to ground the 128 x 8 organization is selected. If the ORG pin is left unconnected, then an internal pull-up device will select the 64 x 16 organization | | | |

| | | | INSTRUCTION SET | | | | | |
|-------------|-----|--------|--------------------------------|--|---------|---------------------------------|-----------------------|--|
| Start | | Start | Address | | Data | | Comments | |
| Instruction | Bit | Opcode | 128 x 8 | 64 × 16 | 128 x 8 | 64 × 16 | | |
| READ | 1 | 10 | A ₆ -A ₀ | A ₅ -A ₀ | | | Read Address AN-A0 | |
| ERASE | 1 | 1 1 | A ₆ -A ₀ | A ₅ -A ₀ | | | ERASE Address AN-A0 | |
| WRITE | 1 | 0 1 | A ₆ -A ₀ | $A_6 - A_0$ $A_5 - A_0$ $D_7 - D_0$ $D_{15} - D_0$ | | D ₁₅ -D ₀ | WRITE Address AN-A0 | |
| EWEN | 1 | 00 | 11XXXXX | 11XXXX | | | Program Enable | |
| EWDS | 1 | 00 | 00XXXXX | 00XXXX | | | Program Disable | |
| ERAL | 1 | 00 | 10XXXXX | 10XXXX | | | Erase All Addresses | |
| WRAL | 1 | 00 | 01XXXXX | 01XXXX | D7-D0 | D ₁₅ -D ₀ | Program All Addresses | |

Power-On Data Protection Circuitry: During power-up all modes of operation are inhibited until V_{CC} has reached a level of between 2.8 and 3.5 volts. During power-down the source data protection circuitry acts to inhibit all modes when V_{CC} has fallen below the voltage range of 2.8 to 3.5 volts.

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ABSOLUTE MAXIMUM RATINGS

| Parameter | Symbol | Condition | Value | Unit |
|---------------------|----------------|-------------|------------------------------|------|
| Supply Voltage | Vcc | CC –0.3 ~ 7 | | V |
| Input Voltage | V ₁ | Ta = 25 °C | -0.3 ~ V _{CC} + 0.3 | V |
| Output Voltage | Vo | | -0.3 ~ V _{CC} + 0.3 | V |
| Storage Temperature | TSTG | | -55 ~ + 150 | °C |

Note: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to the conditions as recommended. Exposure to ABSOLUTE MAXIMUM RATINGS for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE

| Parameter | Symbol | Range | Unit |
|-----------------------|--------|----------|------|
| Supply Voltage | Vcc | 5 ± 10 % | V |
| Temperature Range | Та | -40 ~ 85 | °c |
| Data Hold Temperature | Та | -40 ~ 85 | °C |

DC CHARACTERISTICS

(V_{CC} = 4.5V to 5.5V, Ta = $-40 \sim 85^{\circ}$ C, unless otherwise specified.)

| Parameter | Symbol | Condition | MIN | МАХ | Unit |
|------------------------|--------|---|----------------------|---------------------|------|
| Supply Voltage | Vcc | | 4.5 | 5.5 | V |
| | ICC1 | V _{CC} = 5.5 V CS = 1 | | 5 | mA |
| Power Supply Current | ICC2 | $V_{CC} = 5.5 V$ CS = 0 DI = 0 or V_{CC} | | 100 | μA |
| "L" Input Voltage | VIL | | -0.1 | 0.8 | v |
| "H" Input Voltage | VIH | | 2.0 | V _{CC} + 1 | V |
| | VOL | TTL I _{OL} = 2.1 mA | | 0.4 | V |
| | | CMOS I _{OL} = 100 μA | | 0.1 | V |
| "H" Output Valtara | Val | TTL I _{OH} =400 μA | 2.4 | | V |
| | ⊻он | CMOS I _{OH} = −40µA | V _{CC} -0.5 | | V |
| Input Leakage Current | ILI. | $0 \le V_{IN} \le V_{CC}$ | -15 | 10 | μA |
| Output Leakage Current | 1LO | V _{out} = 5.5 V CS = 0 | | 10 | μA |

| Parameter | Description | Test Condition | Min | Тур | Max | Units |
|--------------------|------------------------------|--|-----|-----|-----|-------|
| tCSS | CS Setup Time | | 0.2 | | | μs |
| ^t CSH | CS Hold Time | | 0 | | | μs |
| tDIS | DI Setup Time | | 0.4 | | | μs |
| tDIH | DI Hold Time | | 0.4 | | | μs |
| ^t PD1 | Output Delay to 1 | CL = 100pF | | | 2 | μs |
| ^t PD0 | Output Delay to 0 | V _{OL} = 0.8V, V _{OH} = 2.0 | | | 2 | μs |
| tHZ | Output Delay to HiZ | V _{IL} = 0.45V, V _{IH} = 2.4 | | | 0.4 | μs |
| tew | Erase / Write Pulse Width | | | | 10 | ms |
| tCSMIN | Min CS Low Time | | 1 | | | μs |
| ^t SKHI | Min SK High Time | | 1 | | | μs |
| ^t SKLOW | Min SK Low Time | | 1 | | | μs |
| tsv | Output Delay to Status Valid | C _L = 100 pF | | | 1 | μs |
| SKMAX | Maximum Frequency | | 0 | | 250 | kHz |

AC CHARACTERISTICS (Vcc = 4.5V to 5.5V, Ta = $-40 \sim 85^{\circ}$ C, unless otherwise specified)



Synchronous Timings

DEVICE OPERATION

The MSM 16811 has 7 instructions that allow it to read, erase, or write. Each instruction consists of a start bit logical '1', an opcode field (2 bits or 4 bits) and an address field (6 or 7 bits).

The DO pin is a multiplexed pin. It is used as Data Out during the Read mode. It can also be used as a Ready Busy status indicator in programming mode. In all the other modes DO is tri-stated.

During power-up, all modes of operation are disabled and the device comes up in a program disabled state. An EWEN instruction has to be issued before starting to program.

At power-down, when V_{CC} falls below a level of approximately 3V, the data protection circuitry inhibits all modes of operation and an EWDS instruction is executed internally.



| Organization | A _N | D _N |
|--------------|----------------|----------------|
| 128 x 8 | A ₆ | D ₇ |
| 64 × 16 | A5 | D15 |

The READ instruction reads the contents of the addressed register. It outputs data serially on the DO pin. After the instruction is decoded, a dummy bit (logical "0") precedes the output data string.

ERASE/WRITE ENABLE AND DISABLE



After power-up and before starting any programming instruction the EWEN instruction has to be issued. Once it has been issued, it will remain active until an EWDS instruction takes place. The EWDS instruction is provided to avoid any accidental programming of the part. The READ instruction is independent from the EWEN and EWDS instructions.

ERASE MODE



After an ERASE instruction has been shifted in. CS is dropped low. This will set the beginning of the self timed erase sequence. If CS is then brought high (after observing t_{CS} spec) the DO pin will act as a status indicator. It will remain low as long as the chip is programming. It will go high after all the bits of the addressed register have been set to a logical '1'.

WRITE MODE



After a WRITE instruction has been shifted in with the corresponding 8 bits or 16 bits of data, CS is dropped low. This will set the beginning of the self timed programming sequence. The addressed register will first be erased and then the previously shifted data will be written in the register. If CS is brought high during the programming time (after observing the t_{CS} specification), the DO pin will act as a status indicator – it will remain low as long as the chip is programming. It will go high after all the bits of the addressed register have been set to their proper value.

| Configuration | A _N | D _N |
|---------------|----------------|-----------------|
| 128 × 8 | A ₆ | D ₇ |
| 64 × 16 | A5 | D ₁₅ |

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ERASE ALL



This instruction is provided to erase the whole chip. Besides its different opcode, the ERAL instruction is identical to the ERASE instruction.

WRITE ALL



This instruction is provided to write simultaneously all the registers. All the registers must be erased before doing a WRAL operation. Besided its different opcode, the WRAL instruction is identical to the WRITE instruction.